			AL
	Application No.	Applicant(s)	
Notice of Allowability	10/813,488	OHTSUKA ET AL.	
Notice of Allowability	Examiner	Art Unit	
	Theresa T. Doan	2814	
The MAILING DATE of this communication apper All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in th or other appropriate communic GHTS. This application is sub	is application. If not include cation will be mailed in due	ed course. THIS
1. This communication is responsive to 10/22/04.			
2. The allowed claim(s) is/are <u>1-3</u> .			
3. \boxtimes The drawings filed on <u>30 March 2004</u> are accepted by the	Examiner.		
4.			
 Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date	6. ☐ Interview Sum Paper No./Ma 8), 7. ☑ Examiner's Am	il Date	ŕ

DETAILED ACTION

EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

This application is in condition for allowance except for the presence of claims 4-15 non-elected without traverse. Accordingly, claims 4-15 been cancelled.

Reasons for Allowance

- 2. Claims 1-3 are allowed.
- 3. The following is an examiner's statement of reasons for allowance:

The prior art of record fails to disclose the combination of a method of fabricating a semiconductor substrate for a compound semiconductor device recited in the base claim 1. Specifically, the combination of the process comprising creating a buffer region by causing a first compound semiconductor to grow epitaxially on the baseplate, the buffer region possibly containing dislocations; creating a dislocation refracting region on a major surface of the buffer region by causing a second compound semiconductor, different from the first compound semiconductor, to grow epitaxially on the major surface of the buffer region, the dislocation refracting region having a major surface with

Art Unit: 2814

a multiplicity of protuberances capable of refracting extensions of the dislocations from the buffer region; and creating a leveling region on the major surface of the dislocation refracting region by causing a third compound semiconductor, different from the second compound semiconductor, to grow epitaxially on the major surface of the dislocation refracting region, the leveling region having a major surface of greater levelness than the major surface of the dislocation refracting region whereby the leveling region is less in dislocation density than the buffer region and the dislocation refracting region as the dislocations created in the buffer region are refracted away from the leveling region by the protuberances on the major surface of the dislocation refracting region.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Theresa T Doan whose telephone number is (571) 272-1704. The examiner can normally be reached on Monday to Thursday from 8:00AM - 6:00PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, WAEL FAHMY can be reached on (571) 272-1705. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Application/Control Number: 10/813,488

Art Unit: 2814

Page 4

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

TD

December 23, 2004.

PHAT X. CAO
PRIMARY EXAMINER